

AI
Cncld

within the contact opening, removing a substantial portion of the contact metal and the barrier layer from the semiconductor substrate and forming a contact plug within the contact opening, and subjecting the contact plug to a temperature sufficient to anneal the barrier layer. In one aspect of this particular embodiment, forming an active device includes forming an active device having a design width of about 0.25 microns or less. ✓



Please delete the present title and insert in its place --A Method of Fabricating A Contact With a Post Contact Plug Anneal--.

IN THE CLAIMS:

Sub
B1
A2

Kindly amend Claim 1 as follows:

1. (Amended) A process for fabricating a contact in a semiconductor substrate having a contact opening formed therein, comprising:

depositing by physical vapor deposition a barrier layer in said contact opening and on at least a portion of said semiconductor substrate;

depositing a contact metal on said barrier layer within said contact opening;

removing a substantial portion of said contact metal and said barrier layer from said semiconductor substrate [and forming] to form a contact plug within said contact opening; and

subjecting said contact plug to a temperature sufficient to anneal said barrier layer.

Kindly cancel Claim 3 without prejudice or disclaimer.

RECEIVED
APR 12 2000
TC 2800 MAIL ROOM